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(54) Title: LASER LIFT-OFF OF SAPPHIRE FROM A NITRIDE FLIP-CHIP

(57) Abstract: In a method for fabricating a flip-chip light emitting diode device, epitaxial layers are deposited on a sapphire growth substrate to produce an epitaxial wafer. A plurality of light emitting diode devices are fabricated on the epitaxial wafer. The epitaxial wafer is diced to generate a device die. The device die is flip chip bonded to a mount. The flip chip bonding includes securing the device die to the mount by bonding at least one electrode of the device die to at least one bonding pad of the mount. Subsequent to the flip chip bonding, the growth substrate of the device die is removed via the application of laser light.



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